



STPS130

POWER SCHOTTKY RECTIFIER

Table 1: Main Product Characteristics

$I_{F(AV)}$	1 A
V_{RRM}	30 V
$T_j(max)$	150°C
$V_F(max)$	0.46 V

FEATURES AND BENEFITS

- Very low forward voltage drop for less power dissipation
- Optimized conduction/reverse losses trade-off which means the highest yield in the applications
- Surface mount miniature packages
- Avalanche capability specified

DESCRIPTION

Single Schottky rectifier suited to Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in SMA and SMB, this device is especially intended for use in parallel with MOSFETs in synchronous rectification and low voltage secondary rectification.

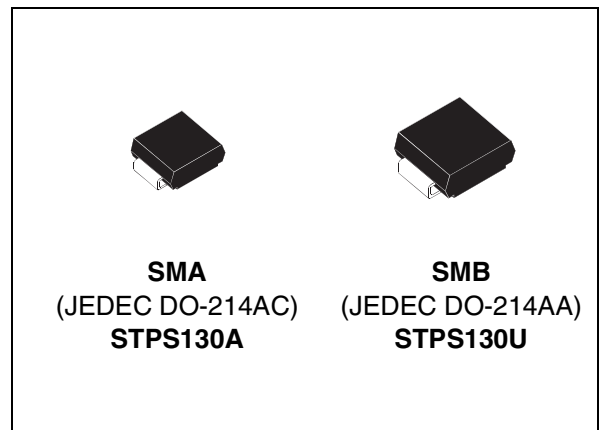


Table 2: Order Codes

Part Number	Marking
STPS130A	S130
STPS130U	G12

Table 3: Absolute Ratings (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		30	V
$I_{F(RMS)}$	RMS forward current		7	A
$I_{F(AV)}$	Average forward current	$T_L = 130^\circ\text{C} \quad \delta = 0.5$	1	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ms}$ sinusoidal	45	A
I_{RRM}	Repetitive peak reverse current	$t_p = 2\mu\text{s} \quad F = 1\text{kHz}$ square	1	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100\mu\text{s}$ square	1	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1\mu\text{s} \quad T_j = 25^\circ\text{C}$	1200	W
T_{stg}	Storage temperature range		-65 to + 150	°C
T_j	Maximum operating junction temperature *		150	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} > \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

Table 4: Thermal Resistance

Symbol	Parameter		Value	Unit
$R_{th(j-l)}$	Junction to lead	SMA	30	$^{\circ}\text{C/W}$
		SMB	23	

Table 5: Static Electrical Characteristics

Symbol	Parameter	Tests conditions		Min.	Typ	Max.	Unit
I_R *	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			10	μA
		$T_j = 125^{\circ}\text{C}$			1.5	10	mA
V_F **	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 1\text{A}$			0.55	V
		$T_j = 125^{\circ}\text{C}$			0.37	0.46	
		$T_j = 25^{\circ}\text{C}$	$I_F = 2\text{A}$			0.63	
		$T_j = 125^{\circ}\text{C}$			0.45	0.55	

Pulse test: * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

** $t_p = 5\text{ ms}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation: $P = 0.37 \times I_F(AV) + 0.090 I_F^2(RMS)$

Figure 1: Average forward power dissipation versus average forward current

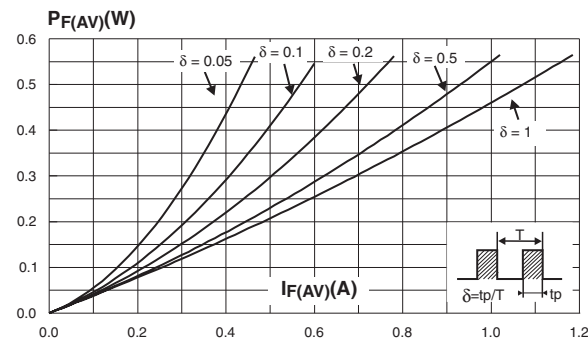
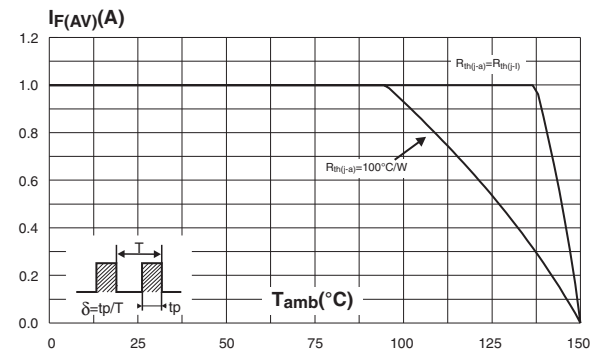
Figure 2: Average forward current versus ambient temperature ($\delta = 0.5$)

Figure 3: Normalized avalanche power derating versus pulse duration

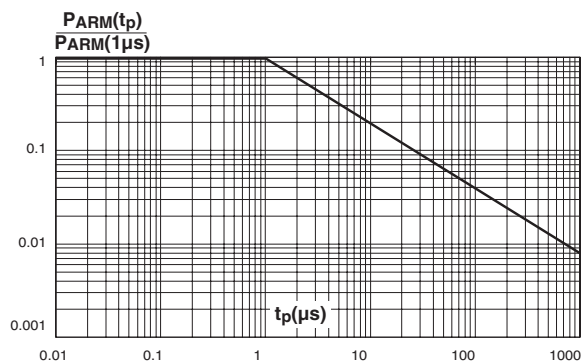


Figure 4: Normalized avalanche power derating versus junction temperature

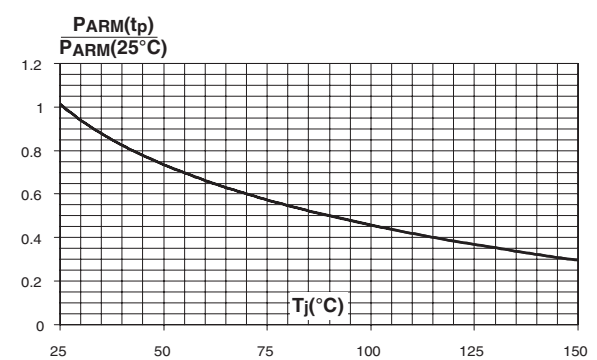


Figure 5: Non repetitive surge peak forward current versus overload duration (maximum values) (SMA)

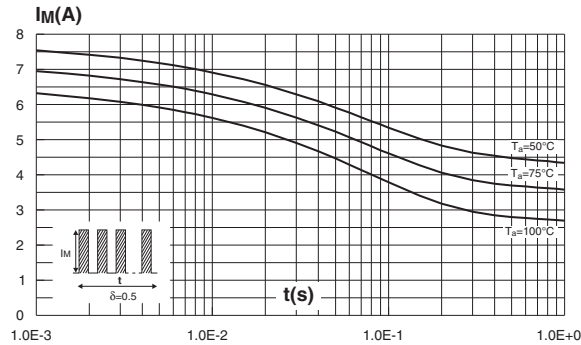


Figure 6: Non repetitive surge peak forward current versus overload duration (maximum values) (SMB)

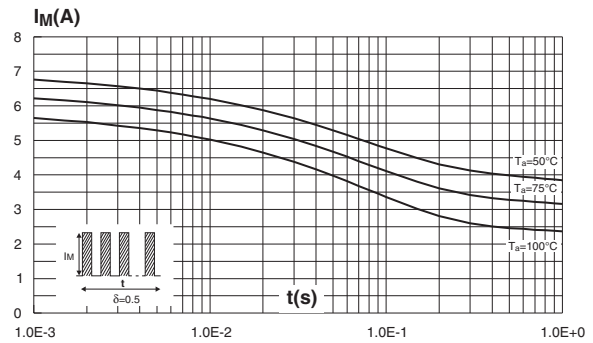


Figure 7: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy printed circuit board, e(Cu)=35μm, recommended pad layout) (SMA)

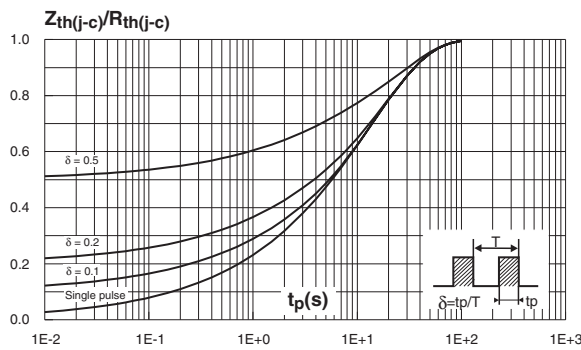


Figure 8: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy printed circuit board, e(Cu)=35μm, recommended pad layout) (SMB)

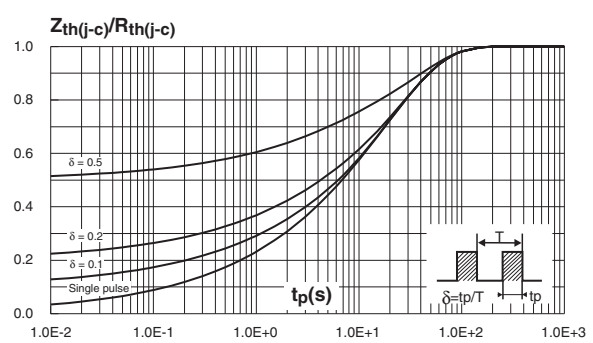


Figure 9: Reverse leakage current versus reverse voltage applied (typical values)

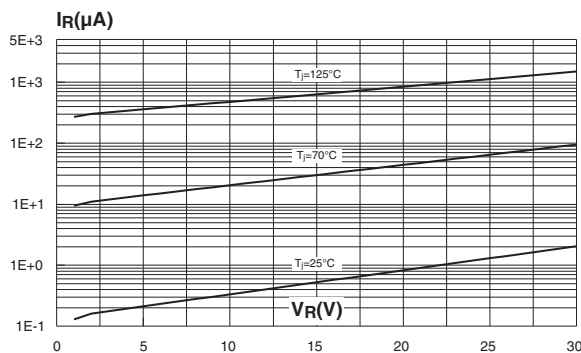


Figure 10: Junction capacitance versus reverse voltage applied (typical values)

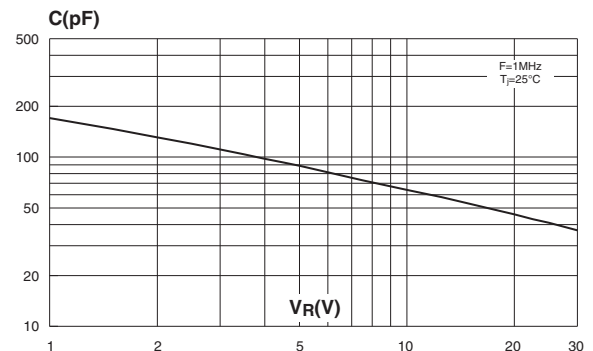


Figure 11: Forward voltage drop versus forward current (maximum values)

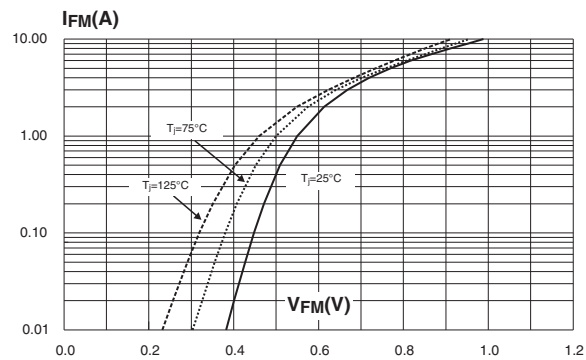


Figure 12: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness: 35 μm) (SMA)

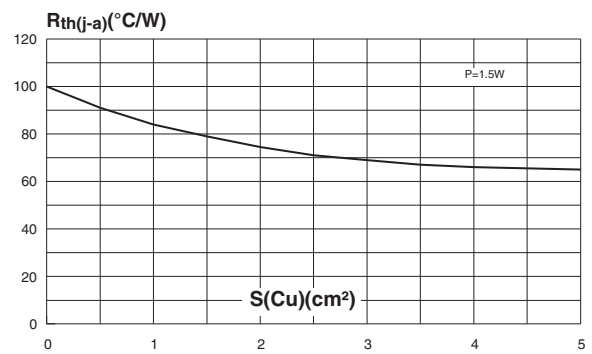


Figure 13: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness: 35 μm) (SMB)

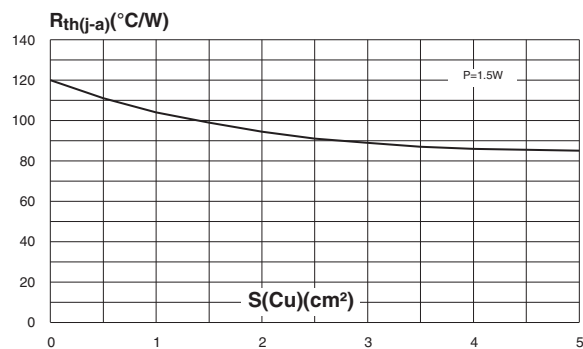


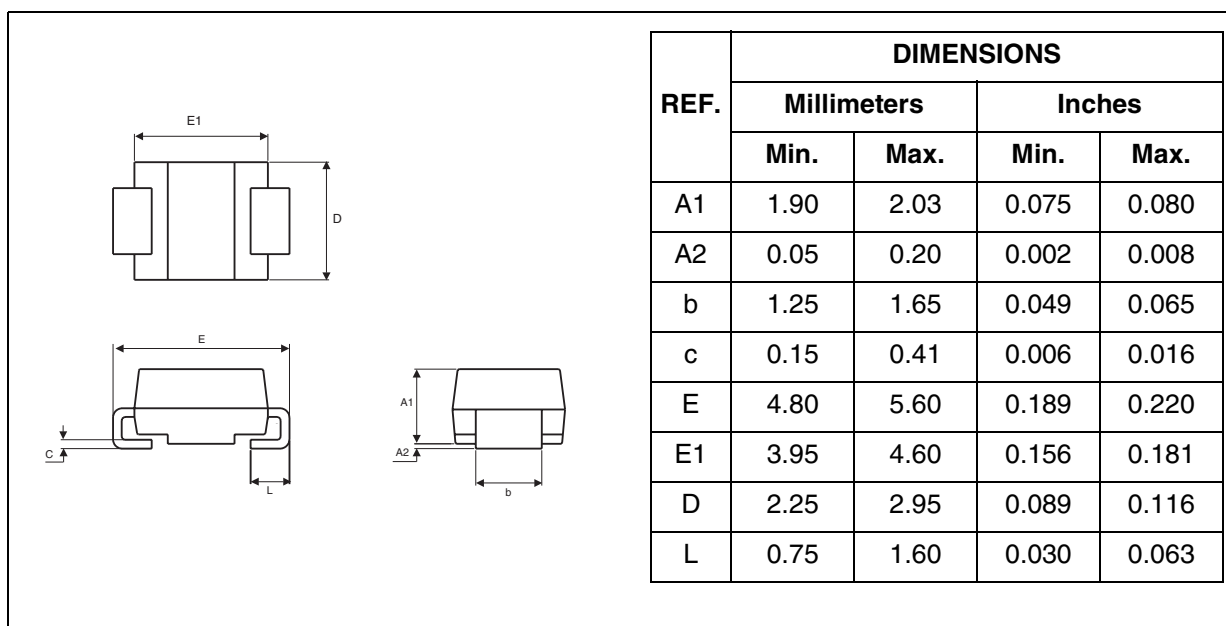
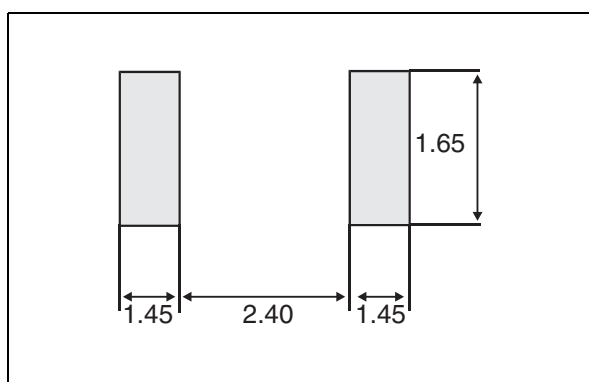
Figure 14: SMA Package Mechanical Data**Figure 15: SMA Foot Print Dimensions**
(in millimeters)

Figure 16: SMB Package Mechanical Data

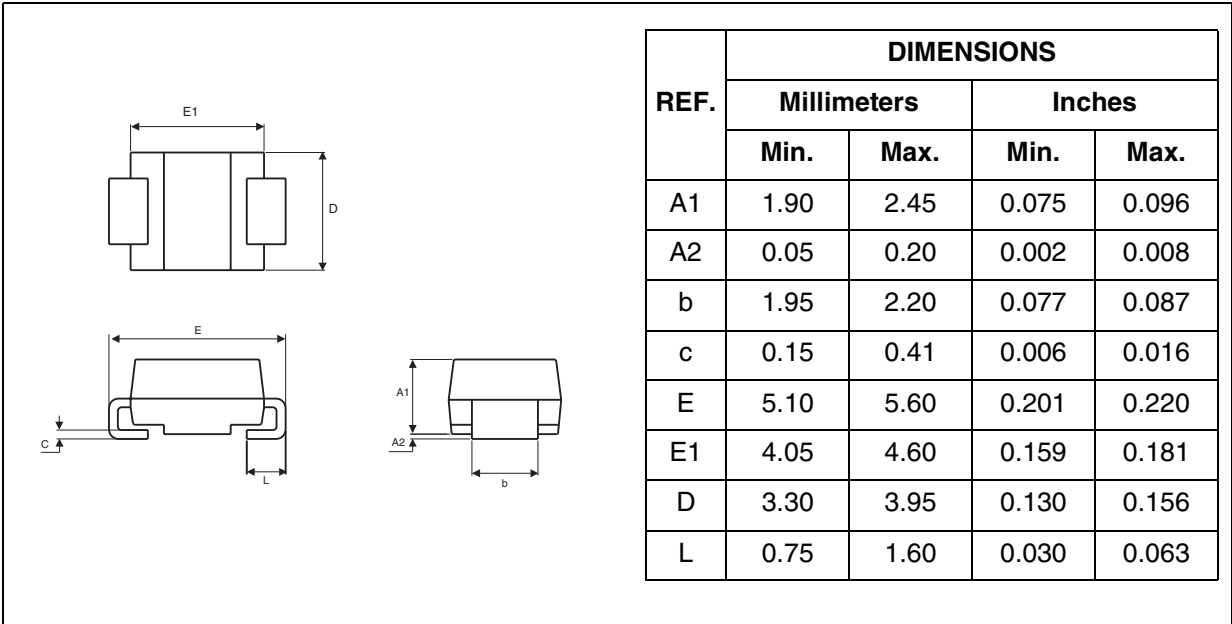


Figure 17: SMB Foot Print Dimensions
(in millimeters)

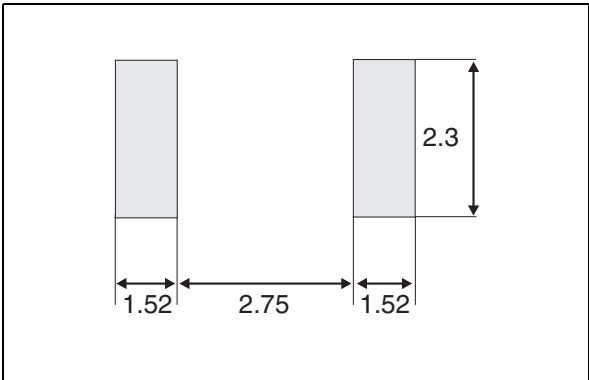


Table 6: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS130A	S130	SMA	0.068 g	5000	Tape & reel
STPS130U	G12	SMB	0.107 g	2500	Tape & reel

- Band indicates cathode
- Epoxy meets UL94, V0

Table 7: Revision History

Date	Revision	Description of Changes
Jul-2003	4A	Last update.
Aug-2004	5	SMA package dimensions update. Reference A1 max. changed from 2.70mm (0.106inc.) to 2.03mm (0.080).

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